03E 08442 [

Zilog

April 1988

T-49-17-07

Z84C00 CMOS Z80® CPU Central Processing Unit

FEATURES

- The CMOS Z80 combines the high performance of the Z80 CPU with extremely low power consumption which results in increased reliability and very low system power requirements. This dramatic power savings makes the CMOS Z80 a natural choice for both hand-held and battery back-up operations.
- Pin compatible with Z80 CPUs.
- Software compatible with Z80 CPUs. The extensive instruction set contains 158 instructions, including the 8080A instruction set as a subset.
- Single 5 volt power supply (± 10%).
- The CMOS Z80 microprocessors and associated family of peripherals can be linked by a vectored interrupt system. This system can be daisy-chained to allow implementation of a priority interrupt scheme.

- Duplicate set of both general-purpose and flag registers.
- Two sixteen bit index registers.
- Three modes of maskable interrupts:
 Mode 0—8080A similar;
 Mode 1—Non-Z80 environment, location 38H;
 Mode 2—Z80 family peripherals, vectored interrupts.
- Low Power Consumption
 15 mA typical Icc
 Standby current less than 100 μA @ 5V
- On-chip dynamic memory refresh counter.
- Can be operated at 6.144MHz clock.

GENERAL DESCRIPTION

The CPUs are fourth-generation enhanced microprocessors with exceptional computational power. They offer higher system throughput and more efficient memory utilization than comparable second- and third-generation microprocessors. The internal registers contain 208 bits of read/write memory that are accessible to the programmer. These registers include two sets of six general-purpose registers which may be used individually as either 8-bit registers or as 16-bit register pairs. In addition, there are two sets of accumulator and flag registers. A group of "Exchange" instructions makes either set of main or alternate registers accessible to the programmer. The alternate set allows operation in foreground-background mode or it may be reserved for very fast interrupt response.

The CPU also contains a Stack Pointer, Program Counter, two index registers, a Refresh register (counter), and an Interrupt register. The CPU is easy to incorporate into a system since it requires only a single +5V power source. All output signals are fully decoded and timed to control standard memory or peripheral circuits; the CPU is supported by an extensive family of peripheral controllers. The internal block diagram (Figure 1) shows the primary functions of the processors. Subsequent text provides more detail on the I/O controller family, registers, instruction set, interrupts and daisy chaining, and CPU timing.

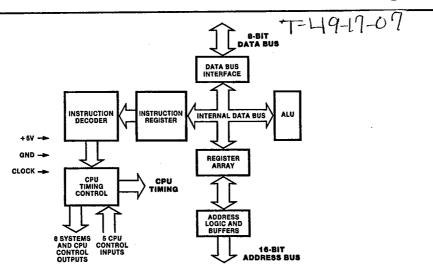


Figure 1. Z80C CPU Block Diagram

CMOS Z80 MICROPROCESSOR FAMILY

The Zilog CMOS Z80 microprocessor is the central element of a comprehensive microprocessor product family. This family works together in most applications with minimum requirements for additional logic, facilitating the design of efficient and cost-effective microcomputer-based systems.

Zilog has designed five components to provide extensive support for the microprocessor. These are:

- The PIO (Parallel Input/Output) operates in both data-byte I/O transfer mode (with handshaking) and in bit mode (without handshaking). The PIO may be configured to interface with standard parallel peripheral devices such as printers, tape punches, and keyboards.
- The CTC (Counter/Timer Circuit) features four programmable 8-bit counter/timers, each of which has an 8-bit prescaler. Each of the four channels may be configured to operate in either counter or timer mode.

- The DMA (Direct Memory Access) controller provides dual port data transfer operations and the ability to terminate data transfer as a result of a pattern match.
- The SIO (Serial Input/Output) controller offers two channels. It is capable of operating in a variety of programmable modes for both synchronous and asynchronous communication, including Bi-Synch and SDLC.
- The DART (Dual Asynchronous Receiver/Transmitter) device provides low cost asynchronous serial communication. It has two channels and a full modem control interface.
- The above peripherals are compatible with the CPU; in addition, the PIO, CTC, and SIO devices are available in CMOS versions.

CPU TIMING

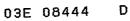
The CPU executes instructions by proceeding through a specific sequence of operations:

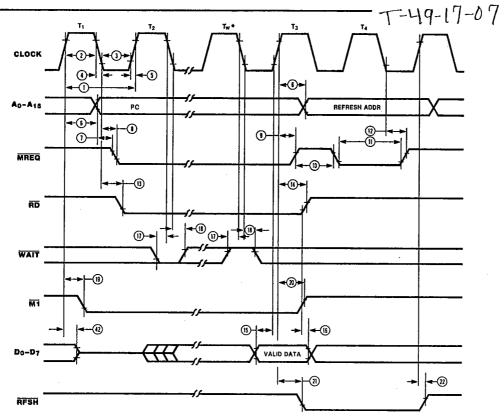
- Memory read or write
- I/O device read or write
- Interrupt acknowledge

The basic clock period is referred to as a T time or cycle, and three or more T cycles make up a machine cycle (M1, M2 or M3 for instance). Machine cycles can be extended either by the CPU automatically inserting one or more Wait states or by the insertion of one or more Wait states by the user.

Instruction Opcode Fetch. The CPU places the contents of the Program Counter (PC) on the address bus at the start of the cycle (Figure 2). Approximately one-half clock cycle later, MREQ goes active. When active, RD indicates that the memory data can be enabled onto the CPU data bus.

The CPU samples the WAIT input with the falling edge of clock state T₂. During clock states T₃ and T₄ of an M1 cycle dynamic RAM refresh can occur while the CPU starts decoding and executing the instruction. When the Refresh Control signal becomes active, refreshing of dynamic memory can take place.





*Tw = Wait cycle added when necessary for slow ancilliary devices

Figure 2. Instruction Opcode Fetch

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Memory Read or Write Cycles. Figure 3 shows the timing of memory read or write cycles other than an opcode fetch (M1) cycle. The MREQ and RD signals function exactly as in the fetch cycle. In a memory write cycle, MREQ also

becomes active when the address bus is stable. The WR line is active when the data bus is stable, so that it can be used directly as an R/W pulse to most semiconductor memories.

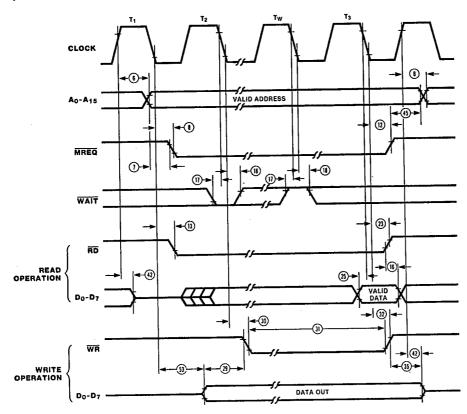
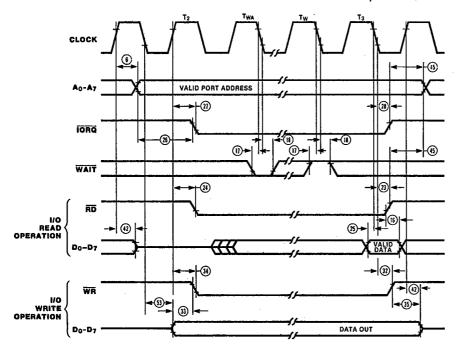


Figure 3. Memory Read or Write Cycles

D

input or Output Cycles. Figure 4 shows the timing for an I/O read or I/O write operation. During I/O operations, the CPU automatically inserts a single Wait state (T_{WA}) . This

extra Wait state allows sufficient time for an I/O port to decode the address from the port address lines.



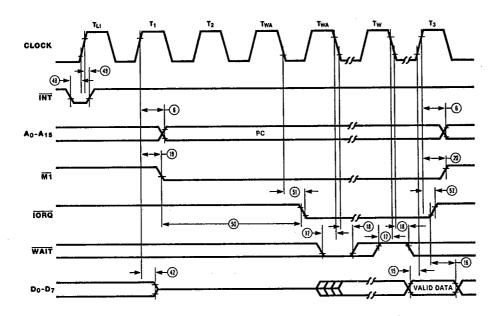
T_{MA} = One wait cycle automatically inserted by CPU.

Figure 4. Input or Output Cycles

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Interrupt Request/Acknowledge Cycle. The CPU samples the interrupt signal with the rising edge of the last clock cycle at the end of any instruction (Figure 5). When an interrupt is accepted, a special M1 cycle is generated.

During this M1 cycle, IORQ becomes active (instead of MREQ) to indicate that the interrupting device can place an 8-bit vector on the data bus. The CPU automatically adds two Wait states to this cycle.



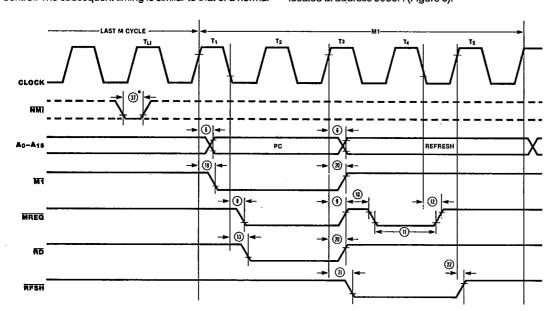
NOTES: 1) T_{ij} = Last state of any instruction cycle. 2) T_{min} = Walt cycle automatically inserted by CPU.

Figure 5. Interrupt Request/Acknowledge Cycle

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Non-Maskable Interrupt Request Cycle. NMI is sampled at the same time as the maskable interrupt input INT but has higher priority and cannot be disabled under software control. The subsequent timing is similar to that of a normal

instruction fetch except that data put on the bus by the memory is ignored. The CPU instead executes a restart (RST) operation and jumps to the NMI service routine located at address 0066H (Figure 6).

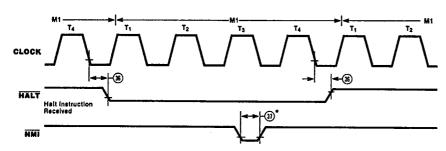


^{*}Although NMI is an asynchronous input, to guarantee its being recognized on the following machine cycle, NMI's falling edge must occur no late than the rising edge of the clock cycle preceding the last state of any instruction cycle (T_L).

Figure 6. Non-Maskable Interrupt Request Operation

Halt Acknowledge Cycle. When the CPU receives a Halt instruction, it executes NOP states until either an INT or NMI input is received. When in the Halt state, the HALT output is

active and remains so until an interrupt is received (Figure 7). INT will also force a Halt exit.



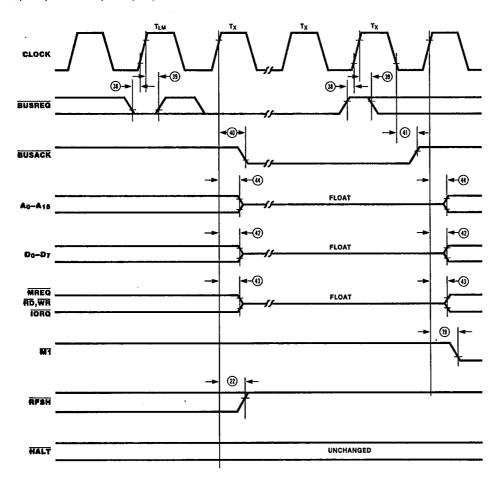
^{*}Although NMI is an asynchronous input, to guarantee its being recognized on the following machine cycle, NMI's falling edge must occur no later than the rising edge of the clock cycle praceding the last state of any instruction cycle (T_L).

Figure 7. Halt Acknowledge Cycle

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Bus Request/Acknowledge Cycle. The CPU samples BUSREQ with the rising edge of the last clock period of any machine cycle (Figure 8). If BUSREQ is active, the CPU sets its address, data, and MREQ, IORQ, RD, and WR lines to a

high-impedance state with the rising edge of the next clock pulse. At that time, any external device can take control of these lines, usually to transfer data between memory and I/O devices.



NOTES: 1) T_{LM} = Last state of any M cycle. 2) T_{χ} = An arbitrary clock cycle used by requesting device.

Figure 8. Z-BUS Request/Acknowledge Cycle

是我们的时候,他们就是一个时间,他们也是一个时间,我们也没有一个时间,他们也是一个时间,他们也是一个时间,他们也是一个时间,他们也是一个时间,他们也是一个时间, 第一天,一个时间,他们就是一个时间,他们就是一个时间,他们就是一个时间,他们就是一个时间,他们就是一个时间,他们就是一个时间,他们就是一个时间,他们也是一个时间

Reset Cycle. RESET must be active for at least three clock cycles for the CPU to properly accept it. As long as RESET remains active, the address and data buses float, and the control outputs are inactive. Once RESET goes inactive,

three internal T cycles are consumed before the CPU resumes normal processing operation. RESET clears the PC register, so the first opcode fetch will be to location 0000H (Figure 9).

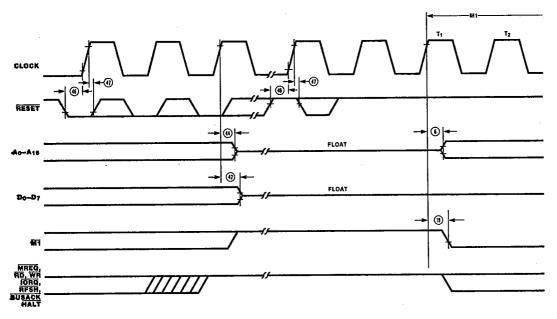


Figure 9. Reset Cycle

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AC CHARACTERISTICS†

T-49-17-07

			Z840	0006
N	umber Symbol	Parameter	Min	Max
1	TcC	Clock Cycle Time	162**	DCc
!	TwCh	Clock Pulse Width (High)	65 ^c	DC°
;	TwCl	Clock Pulse Width (Low)	65°	DC°
ļ	TfC	Clock Fall Time		20°
;	TrC	Clock Rise Time		20°
5	TdCr(A)	Clock to Address Valid Delay		90ª
7	TdA(MREQf)	Address Valid to MREQ Delay	. 35*°	
}	TdCf(MREQf)	Clock to MREQ Delay		70ª
)	TdCr(MREQr)	Clock to MREQ Delay		70 °
lO	TwMREQh	MREQ Pulse Width (High)	65 * °	
11	TwMREQI	MREQ Pulse Width (Low)	135*c	
2	TdCf(MREQr)	Clock to MREQ Delay	•	70 ª
3	TdCf(RDf)	Clock to RD Delay		80ª
4	TdCr(RDr)	Clock to RD Delay		70 ^a
15	TsD(Cr)	Data Setup Time to Clock	30ª	
16	ThD(RDr)	Data Hold Time to RD		0°
17	TsWAIT(Cf)	WAIT Setup Time to Clock	60ª	
8	ThWAIT (Cf)	WAIT Hold Time after Clock	10°	
9	TdCr(M1f)	Clock to M1 Delay		80 ^a
20	TdCr(M1r)	Clock to M1 Delay		80°
21	TdCr(RRSHf)	Clock to RFSH Delay		110ª
22	TdCr(RFSHr)	Clock to RFSH Delay		100 ⁸
13	TdCf(RDr)	Clock to RD Delay		70ª
24	TdCr(RDf)	Clock to RD Delay	_	70ª
25	TsD(Cf)	Data Setup to Clock during M ₂ ,	40°	
		M ₃ , M ₄ , or M ₅ Cycles		<u></u>
26	TdA(lORQf)	Address Stable prior to IORQ	110*c	
27	TdCr(IORQf)	Clock to IORQ Delay		65 4
28	TdCf(lORQr)	Clock to IORQ Delay		70 ^a
29	TdD(WRf)Mw	Data Stable prior to WR	25*°	

^{*}For clock periods other than the minimums shown, calculate parameters using the table on the following page.
Calculated values above assumed TrC = TfC = 20 ns.
†Units in nanoseconds (ns).
†TFor loading ≤ 50 pf. Decrease width by 10 ns for each additional 50 pf.

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AC CHARACTERISTICS† (Continued)

T-49-17-07

			Z840	0006
Nu	mber Symbol	General Parameter	Min	Max
30	TdCf(WRf)	Clock to WR Delay		70ª
31	T₩WR	WR Pulse Width	135 ⁴⁰	
32	TdCf(WRr)	Clock to WR Delay		70°
33	TdD(WRI)IO	Data Stable prior to WR	−55 ^{¢°}	
34	TdCr(WRf)	Clock to WR Delay		60ª
35	TdWRr(D)	Data Stable from WR	30*°	······································
36	TdCf(HALT)	Clock to HALT or		260ª
37	TWNMI	NMI Pulse Width	70°	
38	TsBUSREQ(Cr)	BUSREQ Setup Time to Clock	50ª	
39	ThBUSREQ(Cr)	BUSREQ Hold Time after Clock	25°	
40	TdCr(BUSACKf)	Clock to BUSACK Delay		90ª
41	TdCf(BUSACKr)	Clock to BUSACK Delay		90 4
42	TdCr(Dz)	Clock to Data Float Delay		80 ^c
43	TdCr(CTz)	Clock to Control Outputs		70°
	, ,	Float Delay(MREQ, IORQ,		
		RD, and WR)		
44	TdCr(Az)	Clock to Address Float Delay		80°
45	TdCTr(A)	MREQ , IORQ , RD , and	35*°	····
		WR to Address Hold Time		
46	TsRESET(Cr)	RESET to Clock Setup Time	60ª	
47	ThRESET(Cr)	RESET to Clock Hold Time	10°	
48	TsINT((Cr)	INT to Clock Setup Time	70°	
49	ThINTr(Cr)	NT to Clock Hold Time	10°	
50	TdM1f(lORQf)	M1 to IORQ Delay	365°°	_
51	TdCf(lORQf)	Clock to IORQ Delay		70 ⁸ -
52	TdCf(IORQr)	Clock to IORQ Delay		70 ⁹
53	TdCf(D)	Clock to Data Valid Delay		130 ⁸

^{*}For clock periods other than the minimums shown, calculate parameters using the following table. Calculated values above assumed TrC = TrC = 20 ns.

FOOTNOTES TO AC CHARACTERISTICS

Number	Symbol:	General Paramete	er .	Z84C0006	
1	TcC	TwCh + TwCl + TrC	+ TſC		
7	TdA(MREQf)	TwCh + TfC		-50	
10	TwMREQh	TwCh + TfC		-20	
11	TwMREQI	TcC		30	
26	TdA(IORQf)	TcC		-55	
29	TdD(WRf)	TcC		-140	
31	TwWR	TcC		-30	
33	TdD(WRf)	TwCl + TrC		-140	
35	TdWRr(D)	TwCl + TrC		–55	
45	TdCTr(A)	TwCl + TrC		50	
50	TdM1f(lORQf)	2TcC + TwCh + TfC		–50	
Test Conditions	: V _{IH} = V _{CC'} -1.00V V _{IL} = 0.8 V	VoH = Vcc/2 VoL = Vcc/2	V _{IHC} = V _{CC} -0.6 V V _{H.C} = 0.45 V	FLOAT = ±0.5 V	

[†]Units in nanoseconds (ns).

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ABSOLUTE MAXIMUM RATINGS

Voltages on all pins with respect to V_{SS}. -0.3V to V_{CC} + 0.3V Voltage on all pins with respect to ground.....-0.3V to +7V Operating Case Temperature - 55°C to +125°C Storage Temperature Range - 65°C to +150°C

T-49-17-07

Absolute Maximum Power Dissipation 1W Stresses greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; operation of the device at any condition above those indicated in the operational sections of these specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

STANDARD TEST CONDITIONS

The DC Characteristics and Capacitance sections below apply for the following standard test conditions, unless otherwise noted.

Military Operating Temperature Range (T_C) -55°C to +125°C

Standard Military Test Condition +4.5V ≤ V_{CC} ≤ +5.5V

All voltages are referenced to GND (0V). Positive current flows into the referenced pin.

All AC parameters assume a load capacitance of 100 pf. Add 15 ns delay for each 50 pf increase in load up to a maximum of 200 pf for the data bus. AC timing measurements are referenced to V_{CC}/2 Volts.

^C Guaranteed by Characterization/Design

DC CHARACTERISTICS

Symbol	Parameter	Min	Max	Unit	Condition
VILC	Clock Input Low Voltage	-0.3°	0.45 ^a	v	
VIHC	Clock Input High Voltage	V _{CC} 6 ^a	V _{CC} + .3 ^c	٧	
VIL	Input Low Voltage	-0.3 ^c	0.8ª	٧	
V _{IH}	Input High Voltage	2.2°	V _{CC} c	٧	
VOL	Output Low Voltage		0.4ª	٧	$I_{OL} = 2.0 \text{mA}$
V _{OH1}	Output High Voltage	2.4ª		٧	$I_{OH} = -1.6 \text{mA}$
V _{OH2}	Output High Voltage	V _{CC} - 0.8 ^a		٧	I _{OH} = -250 µA
ICC ₁	Power Supply Current				$V_{CC} = 5V$
·	6 MHz		35°	mA	$V_{IH} = V_{CC} - 0.2V$ $V_{IL} = 0.2V$
Icc ₂	Standby Supply Current		100ª	μΑ	V _{CC} = 5V
					CLK = (0) V _{IH} = V _{CC} - 0.2V V _{IL} = 0.2V
(L)	laput Leakage Current		10 ^a	μΑ	$V_{IN} = 0.4 \text{ to } V_{CC}$
lίO	3-State Output Leakage Current in Float	- 10 ⁸	10 ²⁸	μΑ	V _{OUT} = 0.4 to V _{CC}

Measurements made with outputs floating.
 A₁₅-A₀, D₇-D₀, MREQ, IORQ, RD, and WR.

Unmeasured pins returned to ground.

CAPACITANCE

Symbol .	Parameter		Min	Max	Unit
C _{IN}	Input Capacitance			10°	pf
C _{OUT}	Output Capacitance			15°	pf
OTES:		Parameter Test Status:			·
$I_A = 25$ °C, $f = 1$ MHz.		8 Tested	C Guaran	teed by Characteriz	ation/Decian

a Tested

b Guaranteed

lCO2 standby supply current is guaranteed only when the supplied clock is stopped at a low level during T4 of the machine cycle immediately following the execution of a HALT instruction.

^{4.} Icc, is measured with 100pF capacitive only test load.

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PIN DESCRIPTIONS

7-49-17-07le One (output, active Low). $\overline{M1}$, toge

A₀-A₁₅. Address Bus (output, active High, 3-state). A₀-A₁₅ form a 16-bit address bus. The Address Bus provides the address for memory data bus exchanges (up to 64K bytes) and for I/O device exchanges.

BUSACK. Bus Acknowledge (output, active Low). Bus Acknowledge indicates to the requesting device that the CPU address bus, data bus, and control signals MREQ, IORQ, RD, and WR have entered their high-impedance states. The external circuitry can now control these lines.

BUSREQ. Bus Request (input, active Low). Bus Request has a higher priority than \$\overline{NMI}\$ and is always recognized at the end of the current machine cycle. \$\overline{BUSREQ}\$ forces the CPU address bus, data bus, and control signals \$\overline{MREQ}\$, \$\overline{IORQ}\$, \$\overline{RD}\$, and \$\overline{WR}\$ to go to a high-impedance state so that other devices can control these lines. \$\overline{BUSREQ}\$ is normally wired-OR and requires an external pullup for these applications. Extended \$\overline{BUSREQ}\$ periods due to extensive DMA operations can prevent the CPU from properly refreshing dynamic RAMs.

D₀-D₇. Data Bus (input/output, active High, 3-state). D₀-D₇ constitute an 8-bit bidirectional data bus, used for data exchanges with memory and I/O.

Halt. Halt State (output, active Low). HALT indicates that the CPU has executed a Halt instruction and is awaiting either a nonmaskable or a maskable interrupt (with the mask enabled) before operation can resume. While halted, the CPU executes NOPs to maintain memory refresh.

INT. Interrupt Request (input, active Low). Interrupt Request is generated by I/O devices. The CPU honors a request at the end of the current instruction if the internal software-controlled interrupt enable flip-flop (IFF) is enabled. INT is normally wired-OR and requires an external pullup for these applications.

IORQ. Input/Output Request (output, active Low, 3-state). IORQ indicates that the lower half of the address bus holds a valid I/O address for an I/O read or write operation. IORQ is also generated concurrently with M1 during an interrupt acknowledge cycle to indicate that an interrupt response vector can be placed on the data bus.

M1. Machine Cycle One (output, active Low). M1, together with MREQ, indicates that the current machine cycle is the opcode fetch cycle of an instruction execution. M1, together with IORQ, indicates an interrupt acknowledge cycle.

MREQ. Memory Request (output, active Low, 3-state). MREQ indicates that the address bus holds a valid address for a memory read or memory write operation.

NMI. Non-Maskable Interrupt (input, negative edge-triggered). NMI has a higher priority than INT. NMI is always recognized at the end of the current instruction, independent of the status of the interrupt enable flip-flop, and automatically forces the CPU to restart at location 0066H.

RD. Read (output, active Low, 3-state). RD indicates that the CPU wants to read data from memory or an I/O device. The addressed I/O device or memory should use this signal to gate data onto the CPU data bus.

RESET. Reset (input, active Low). RESET initializes the CPU as follows: it resets the interrupt enable flip-flop, clears the PC and Registers I and R, and sets the interrupt status to Mode 0. During reset time, the address and data bus go to a high-impedance state, and all control output signals go to the inactive state. Note that RESET must be active for a minimum of three full clock cycles before the reset operation is complete.

RFSH. Refresh (output, active Low). RFSH, together with MREQ, indicates that the lower seven bits of the system's address bus can be used as a refresh address to the system's dynamic memories.

WAIT. Wait (input, active Low). WAIT indicates to the CPU that the addressed memory or I/O devices are not ready for a data transfer. The CPU continues to enter a Wait state as long as this signal is active. Extended WAIT periods can prevent the CPU from refreshing dynamic memory properly.

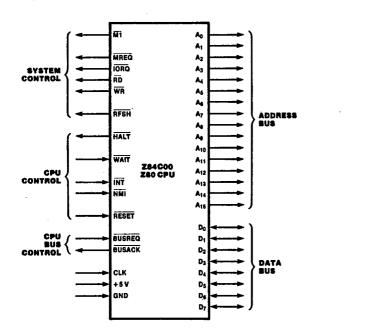
WR. Write (output, active Low, 3-state). WR indicates that the CPU data bus holds valid data to be stored at the addressed memory or I/O location.

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PACKAGE PIN OUTS

T-49-17-07



40 A10 39 A2 38 A3 37 A7 38 A6 35 A6 24 WAIT
23 BUSACK
22 WR
21 RD

DIP and LCC Pin Functions

40-Pin Dual-in-Line Package (DIP), Pin Assignments, Top View

03E 08456

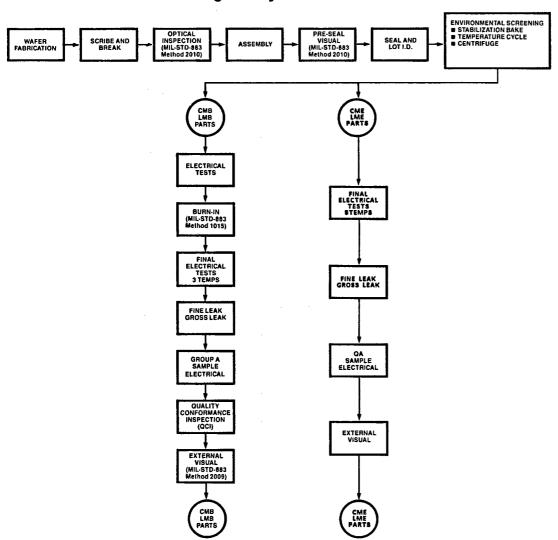
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MIL-STD-883 MILITARY PROCESSED PRODUCT

T-49-17-07

- Mil-Std-883 establishes uniform methods and procedures for testing microelectronic devices to insure the electrical, mechanical, and environmental integrity and reliability that is required for military applications.
- Mil-Std-883 Class B is the industry standard product assurance level for military ground and aircraft application.
- The total reliability of a system depends upon tests that are designed to stress specific quality and reliability concerns that affect microelectronic products.
- The following tables detail the 100% screening and electrical tests, sample electrical tests, and Qualification/Quality Conformance testing required.

Zilog Military Product Flow



Method 5004

9984043 ZILOG INC

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T-49-17-07-Table I MIL-STD-883 Class B Screening Requirements

2010		Requiremen
	Condition B	100%
1008	Condition C	100%
1010	Condition C	100%
2001	Condition E or D ^(Note 1) , Y ₁ Axis Only	100%
	Zilog Military Electrical Specification Static/DC T _C = +25°C	100%
1015	Condition D ^(Note 2) , 160 hours, $T_A = +125$ °C	100%
	Zilog Military Electrical Specification Static/DC T _C = +25°C	100%
	PDA = 5%	100%
	Zilog Military Electrical Specification Static/DC T _C = +125°C, -55°C Functional, Switching/AC T _C = +25°C	100%
1014	Condition B	100%
1014	Condition C	100%
	·	
5005	(See Table II)	Sample
		Sample
	•	Sample
5005	(See Table V)	Sample
2009		100%
		100%
	1008 1010 2001 1015 1015 1014 1014 5005 5005 5005 5	1008 Condition C 1010 Condition C 2001 Condition E or D(Note 1), Y1 Axis Only Zilog Military Electrical Specification Static/DC TC = +25°C 1015 Condition D(Note 2), 160 hours, TA = +125°C Zilog Military Electrical Specification Static/DC TC = +25°C PDA = 5% Zilog Military Electrical Specification Static/DC TC = +125°C, -55°C Functional, Switching/AC TC = +25°C 1014 Condition B 1014 Condition C 5005 (See Table II) 5005 (See Table IV) 5005 (See Table IV) 5005 (See Table V)

NOTES:

mass of >5 grams.

2. In process of fully implementing of Condition D Burn-In Circuits. Contact factory for copy of specific burn-in circuit available.

3. Performed periodically as required by Mil-Std-883, paragraph 1.2.1 b(17).

^{1.} Applies to larger packages which have an inner seal or cavity perimeter of two inches or more in total length or have a package

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00436

Table II Group A Sample Electrical Tests MIL-STD-883 Method 5005

T-49-17-07

Subgroup	Tests	Temperature (T _C)	LTPD Max Accept = 2
Subgroup 1	Static/DC	+25°C	2
Subgroup 2	Static/DC	+125°C	3
Subgroup 3	Static/DC	-55°C	5
Subgroup 7	Functional	+25°C	2
Subgroup 8	Functional	-55°C and +125°C	5
Subgroup 9	Switching/AC	+25°C	2
Subgroup 10	Switching/AC	+125°C	3
Subgroup 11	Switching/AC	−55°C	5

NOTES:

A single sample may be used for all subgroup testing. Where required size exceeds the lot size, 100% inspection shall be allowed.

Group A testing by subgroup or within subgroups may be performed in any sequence unless otherwise specified.

[•] The specific parameters to be included for tests in each subgroup shall be as specified in the applicable detail electrical specification. Where no parameters have been identified in a particular subgroup or test within a subgroup, no Group A testing is required for that subgroup or test.

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Table III Group B

Sample Test Performed Every Week to
Test Construction and insure integrity of Assembly Process. MIL-STD-883 Method 5005

Subgroup	Mil-Std-883 Method	Test Condition	Quantity or LTPD/Max Accept
Subgroup 1 Physical Dimensions	2016		2/0
Subgroup 2 Resistance to Solvents	2015		4/0
Subgroup 3 Solderability	2003	Solder Temperature +245°C ± 5°C	15(Note 1)
Subgroup 4 Internal Visual and Mechanical	2014		1/0
Subgroup 5 Bond Strength	2011	С	15 ^(Note 2)
Subgroup 6(Note 3) Internal Water Vapor Content	1018	1000 ppm. maximum at +100°C	3/0 or 5/1
Subgroup 7 ^(Note 4) Seal 7a) Fine Leak 7b) Gross Leak	1014	7a) B 7b) C	5
Subgroup 8 ^(Note 5) Electrostatic Discharge Sensitivity	3015	Zilog Military Electrical Specification Static/DC T _C = +25°C A = 20-2000V B = >2000V Zilog Military Electrical Specification Static/DC T _C = +25°C	15/0

NOTES:

- Number of leads inspected selected from a minimum of 3 devices.
 Number of bond pulls selected from a minimum of 4 devices.
 Test applicable only if the package contains a dessicant.
 Test not required if either 100% or sample seal test is performed between final electrical tests and external visual during Class B screening.
 Test required for initial qualification and product redesign.

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T-49-17-07 Table IV Group C
Sample Test Performed Periodically to Verify Integrity of the Die.
MIL-STD-883 Method 5005

Subgroup	Mil-Std-883 Method	Test Condition	Quantity or LTPD/Max Accept
Subgroup 1			·····
Steady State Operating Life	1005	Condition D ^(Note 1) , 1000 hours at + 125°C	5
End Point Electrical Tests		Zilog Military Electrical Specification T _C = +25°C, +125°C, -55°C	
Subgroup 2			
Temperature Cycle	1010	Condition C	
Constant Acceleration (Centrifuge)	2001	Condition E or D(Note 2), Y1 Axis Only	
Seal	1014		15
2a) Fine Leak		2a) Condition B	
2b) Gross Leak		2b) Condition C	
Visual Examination	1010 or 1011		
End Point Electrical Tests		Zilog Military Electrical Specification T _C = +25°C, +125°C, -55°C	

NOTE:

NOTE:

1. In process of fully implementing Condition D Burn-In Circuits. Contact factory for copy of specific burn-in circuit available.

2. Applies to larger packages which have an inner seal or cavity perimeter of two inches or more in total length or have a package mass of ≥5 grams.

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Table V Group D
Sample Test Performed Periodically to Insure Integrity of the Package.
MiL-STD-883 Method 5005

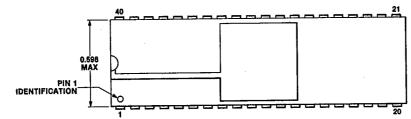
Subgroup	Mil-Std-883 Method	Test Condition	Quantity or LTPD/Max Accep
Subgroup 1			· · · · · · · · · · · · · · · · · · ·
Physical Dimensions	2016		15
Subgroup 2 Lead Integrity	2004	Condition B ₂ or D ^(Note 1)	15
Subgroup 3 Thermal Shock	1011	Condition B minimum, 15 cycles minimum	
Temperature Cycling	1010	Condition C, 100 cycles minimum	15
Moisture Resistance	1004		
Seal 3a) Fine Leak 3b) Gross Leak	1014	3a) Condition B 3b) Condition C	
Visual Examination End Point Electrical Tests	1004 or 1010	Zilog Military Electrical Specification T _C = +25°C, +125°C, -55°C	
Subgroup 4 Mechanical Shock	2002	Condition B minimum	
Vibration Variable Frequency	2007	Condition A minimum	
Constant Acceleration (Centrifuge)	2001	Condition E or D ^(Note 2) , Y ₁ Axis Only	15
Seal 4a) Fine Leak 4b) Gross Leak	1014	4a) Condition B 4b) Condition C	
Visual Examination	1010 or 1011		
End Point Electrical Tests	•	Zilog Military Electrical Specification T _C = +25°C, +125°C, -55°C	
Subgroup 5 Salt Atmosphere	1009	Condition A minimum	
Seal 5a) Fine Leak 5b) Gross Leak	1014	5a) Condition B 5b) Condition C	15
Visual Examination	1009		
Subgroup 6 Internal Water Vapor Content	1018	5,000 ppm. maximum water content at +100°C	3/0 or 5/1
Subgroup 7(Note 3) Adhesion of Lead Finish	2025		15(Note 4)
Subgroup 8 ^(Note 5) Lid Torque	2024		5/0

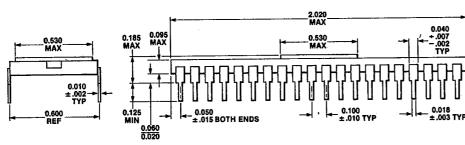
- Lead Integrity Condition D for leadless chip carriers.
 Applies to larger packages which have an inner seal or cavity perimeter of two inches or more in total length or have a package mass of ≥5 grams.
- 3. Not applicable to leadless chip carriers.
- 4. LTPD based on number of leads.
- 5. Not applicable for solder seal packages.

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PACKAGE INFORMATION





40-Pin Ceramic Dual In-line Package (DIP)

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9984043 ZILOG INC

03E 08463

ORDERING INFORMATION

T-49-17-07

CMOS Z80 CPU, 6.0 MHz

40-pin DIP Z84C0006CME Z84C0006CMB

Codes

PACKAGE C = Ceramic

TEMPERATURE $M = -55^{\circ}C$ to $+125^{\circ}C$ **ENVIRONMENTAL** E = Hermetic Standard

Longer Lead Time B = 833 Class B Military

Example: Z84C0006CMB is a CMOS 8400, 6MHz, Ceramic, -55 C to 125 C 883C Standard Flow.

